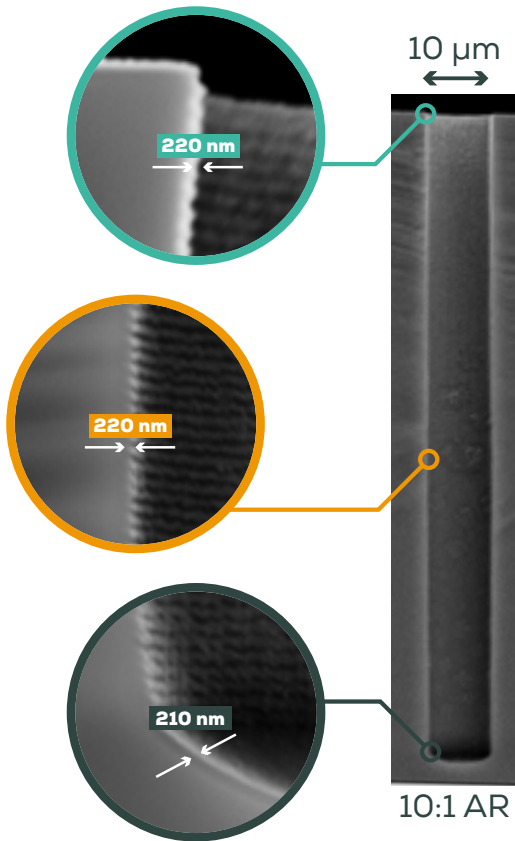


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F.A.S.T.
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*J.Sakar, Sputtering Materials for VLSI and Thin Film Devices, Elsevier Science 2010

